

## SPECIFICATION OF LED CHIP C750-40P [INFRARED]

### 1) Commodity Type and Physical Characteristics.

- |                      |                     |                  |                  |
|----------------------|---------------------|------------------|------------------|
| 1. Material          | GaAlAs/GaAlAs (DDH) |                  |                  |
| 2. Electrode         | Top Side            | N (cathode) side | : Au Alloy & Pad |
|                      | Bottom Side         | P (anode) side   | : Au Alloy       |
| 3. Electrode Pattern |                     |                  | Fig.1            |
| 4. Chip Size         |                     |                  | Fig.2            |
| 5. Chip Thickness    |                     |                  | Fig.2            |
| 6. Emission Area     |                     |                  | Fig.2            |

### 2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=20mA		1.50	1.90	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.0	3.5		mW
Peak Wavelength	$\lambda_P$	If=20mA	735	750	765	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		30		nm
Rise Time	tr	If=20mA		80		ns
Full time	tf	If=20mA		80		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

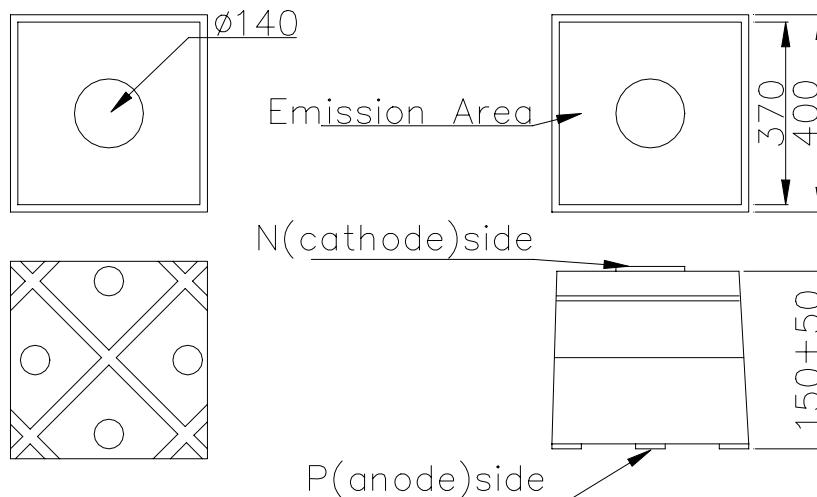


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area